

<b>Notice of References Cited</b>	Application/Control No. 10/637,107	Applicant(s)/Patent Under Reexamination SANDHU ET AL.	
	Examiner Jeff Vockrodt	Art Unit 2822	Page 1 of 1

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-4,960,732	10-1990	Dixit et al.	438/628
	B	US-4,998,151	03-1991	Korman et al.	257/328
	C	US-5,242,860	09-1993	Nulman et al.	438/653
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	WO 86/01640	03-1986	WO	Dean et al.	
	O					
	P					
	Q					
	R					
	S					
	T					

**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Eizenberg et al., TiCN: A new chemical vapor deposited contact barrier metallization for submicron devices, Appl. Phys. Lett. 6 (19), 7 November 1994, pp. 2416-18
	V	Peng et al., Properties of CVD-W Overgrowth on PVD and MOCVD TiN Layers, IEEE, 5th International Conference Proceeding on Solid-State and Integrated Circuit Technology, 1998, pp. 211-214
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.